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ABSTRACT

5 A magnetic memory cell is disclosed having a
structure that prevents disruptions to the magnetization
in the sense layer of the magnetic memory cell. In one
embodiment, the structure includes a high permeability
magnetic film that serves as a keeper for the sense
layer magnetization. The keeper structure provides a
flux closure path that directs demagnetization fields
away from the sense layer. In another embodiment, the
10 structure contains a hard ferromagnetic film that
applies a local magnetic field to the sense layer in the
magnetic memory cell.

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